

METHOD OF FABRICATING SEMICONDUCTOR DEVICE HAVING TRIPLE LDD  
STRUCTURE AND LOWER GATE RESISTANCE FORMED WITH A SINGLE IMPLANT  
PROCESS

5 ABSTRACT OF THE INVENTION

A method of fabricating a semiconductor device having a triple LDD (lateral diffused dopants) structure is disclosed. This fabrication method requires a single implant process, leading to reduction in fabrication costs and fabrication time. Moreover, this fabrication method increases the surface area of the gate structure of the semiconductor device that is available for silicide to be formed, leading to  
10 lower gate resistance.